

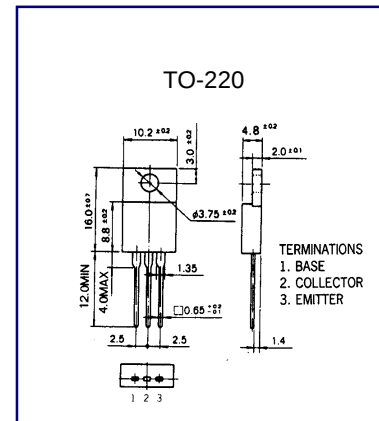


**2SD288**

**NPN EPITAXIAL SILICON TRANSISTOR**

**LOW FREQUENCY POWER AMPLIFIER**

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### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ )

| Characteristic                                   | Symbol    | Rating  | Unit             |
|--------------------------------------------------|-----------|---------|------------------|
| Collector-Base Voltage                           | $V_{CB0}$ | 8.0     | V                |
| Collector-Emitter Voltage                        | $V_{CE0}$ | 55      | V                |
| Emitter-Base voltage                             | $V_{EB0}$ | 5       | V                |
| Collector Current (DC)                           | $I_C$     | 3       | A                |
| Collector Dissipation ( $T_c=25^\circ\text{C}$ ) | $P_C$     | 20      | W                |
| Junction Temperature                             | $T_j$     | 150     | $^\circ\text{C}$ |
| Storage Temperature                              | $T_{stg}$ | -50~150 | $^\circ\text{C}$ |

### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ )

| Characteristic                        | Symbol        | Test Condition                         | Min | Typ | Max | Unit          |
|---------------------------------------|---------------|----------------------------------------|-----|-----|-----|---------------|
| Collector Cutoff Current              | $I_{CBO}$     | $V_{CB}=50\text{V}$ , $I_E=0$          |     |     | 50  | $\mu\text{A}$ |
| DC Current Gain                       | $h_{FE1}$     | $V_{CE}=5\text{V}$ , $I_C=0.5\text{A}$ | 40  |     | 240 | V             |
| Collector- Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=1\text{A}$ , $I_B=0.1\text{A}$    |     |     | 1.0 | V             |
| Current Gain Bandwidth Product        |               |                                        |     |     |     |               |